

Supplementary Information

The gas-phase reaction between silylene and 2-butyne: kinetics, isotope studies, pressure dependence studies and quantum chemical calculations.

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Fig. S3 Pressure dependence of second order rate constants for reaction (D), SiD₂ + MeC≡CMe, in the presence of SF₆ at five temperatures (indicated).

Table S1 Calculated enthalpies (Hartrees) for several species by various different methods

Species	G3B3	G3MP2	G3Q	CBS-Q	CBS-QB3
SiH ₂	-290.454684	-290.172922	-290.453102	-290.16017	-290.161403
2-butyne	-155.830293	-155.678744	-155.823469	-155.648155	-155.647968
2,3-dimethylsilirene	-446.367031	-446.933128	-446.359864	-445.894405	-445.892620

Table S2 .(see next page)

Table S3 Temperature dependent parameters used in RRKM calculations for 2,3-dimethylsilirane-d₂ decomposition

	<i>T</i> /K				
	296	368	430	523	612
TSa wavenumbers ^a /cm	41	46	49	54	56
	35	41	43	47	49
	35	40	42	46	48
	33	38	41	44	46
Z _{LJ} (SF ₆)/10 ⁻¹⁰ cm ³ molecule ⁻¹ s ⁻¹	4.61	4.75	4.87	5.04	5.20

^a Obtained by scaling SiD₂ and ring stretch modes (588, 513, 500, 484 cm⁻¹) by same factors as for 2,3-dimethylsilirene (paper, Table 7).

Table S2 Molecular and transition state parameters for RRKM calculations for 2,3-dimethylsilirene-d₂ decomposition at 612 K

	2,3-dimethylsilirene-d ₂	TSa(d ₂)
$\tilde{\nu}/\text{cm}^{-1}$	2917(1)	2917(1)
	2914(3)	2914(3)
	2858(1)	2858(1)
	2855(1)	2855(1)
	1656(1)	1656(1)
	1524(1)	1524(1)
	1515(1)	1515(1)
	1455(1)	1455(1)
	1452(2)	1452(2)
	1451(1)	1451(1)
	1390(1)	1390(1)
	1386(1)	1386(1)
	1199(1)	1199(1)
	1065(1)	1065(1)
	1044(1)	1044(1)
	1040(1)	1040(1)
	1001(1)	1001(1)
	846(1)	715(1)
	715(1)	627(1)
	627(1)	326(1)
	588(1)	308(1)
	513(1)	205(1)
	500(1)	189(1)
	484(1)	116(1)
	326(1)	101(1)
	308(1)	56(1)
	205(1)	49(1)
	189(1)	48(1)
	116(1)	46(1)
	101(1)	
reaction coordinate/cm ⁻¹	846	
path degeneracy	1	
$E_0(\text{critical energy})/\text{kJ mol}^{-1}$	186.2	
Collision number (in SF ₆)	5.20	
$Z_{LJ}/10^{-10} \text{ cm}^3 \text{ molecule}^{-1} \text{ s}^{-1}$		

Note on Collision Numbers

Leonard-Jones collision numbers were calculated by the procedure recommended by Troe^{S1}. The required parameters are shown in Table S3 below. Since no measurement is possible it was assumed that the LJ parameters for SiH₂ were the same as those for SiH₄^{S2}. For CH₃C≡CCH₃, the parameters were estimated by comparison with those for related molecules^{S2}. These lead to the value of $5.72 \times 10^{-10} \text{ cm}^3 \text{ molecule}^{-1} \text{ s}^{-1}$. The calculated collision efficiency is shown, together with those for related reactions^{S3}, in Table S4.

References

- S1. J. Troe, *J. Chem. Phys.*, 1977, **66**, 4758.
S2. R. C. Reid, J. M. Prausnitz and B. E. Poling, *The properties of Gases and Liquids*, 4th edn., McGraw-Hill, New York, 1988.
S3. R. Becerra and R. Walsh, *J. Organometallic Chem.*, 2001, **636**, 49.

Table S4 Some Lennard-Jones parameters

Molecule or reaction	$\sigma/\text{\AA}$	$(\epsilon/k)\text{K}$
SiH ₂	4.08	207.6
CH ₃ C≡CCH ₃	5.18	317
SiH ₂ + CH ₃ C≡CCH ₃	4.63	256.5

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Table S5 Lennard-Jones collision efficiencies^{b,c} at 298 K for some addition reactions of SiH₂

Substrate	k^a	Z_{LJ}^a	%Efficiency
C ₂ H ₄ ^b	3.5	4.92	71
C ₃ H ₆ ^b	3.4	5.31	64
C ₂ H ₂ ^b	4.0	4.90	82
CH ₃ C≡CCH ₃ ^c	4.3	5.72	75

^a Units: $10^{-10} \text{ cm}^3 \text{ molecule}^{-1} \text{ s}^{-1}$.

^b Reference S3.

^c This work

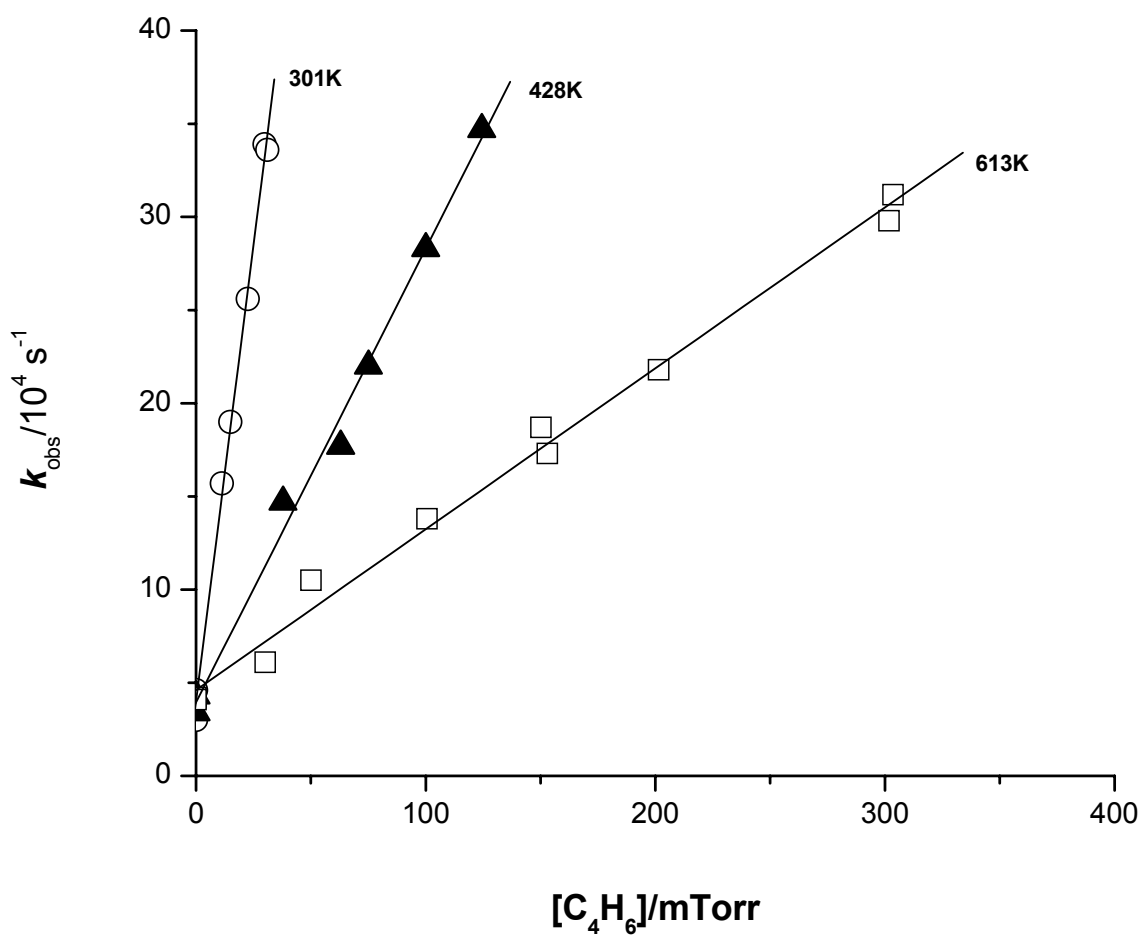


Fig. S1 Second order plots for reaction (H), $\text{SiH}_2 + \text{MeC}\equiv\text{CMe}$, at 10 Torr (He) at three temperatures (indicated).

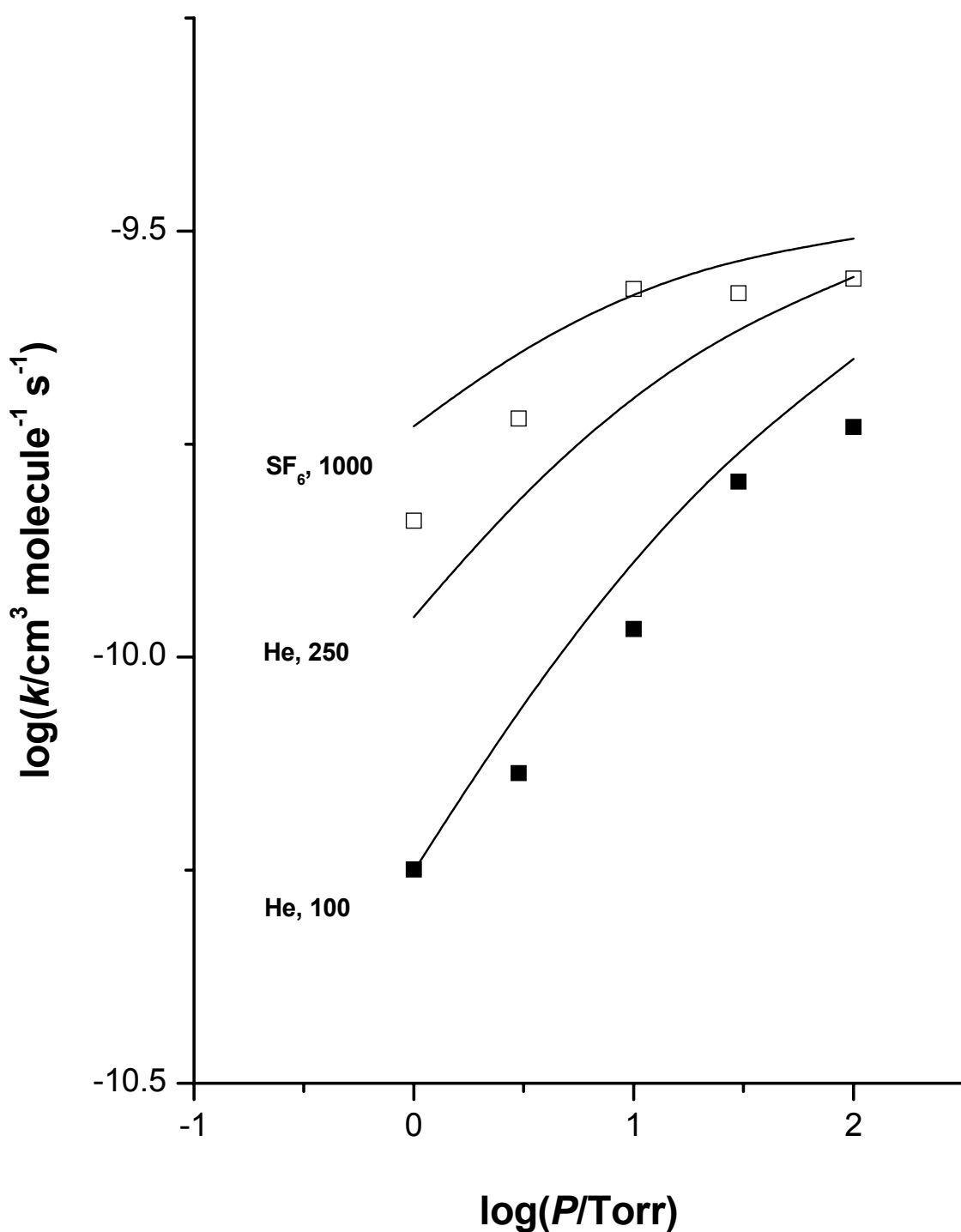


Fig. S2 Comparison of RRKM theoretical curves with experiment for pressure dependence of $\text{SiH}_2 + \text{MeC}\equiv\text{CMe} \rightarrow 2,3\text{-dimethylsilirene}$ in both He (filled symbols) and SF_6 (open symbols) at 429 K and several different energy removal parameters ($\langle \Delta E \rangle_{\text{down}}/\text{cm}^{-1}$), as indicated.

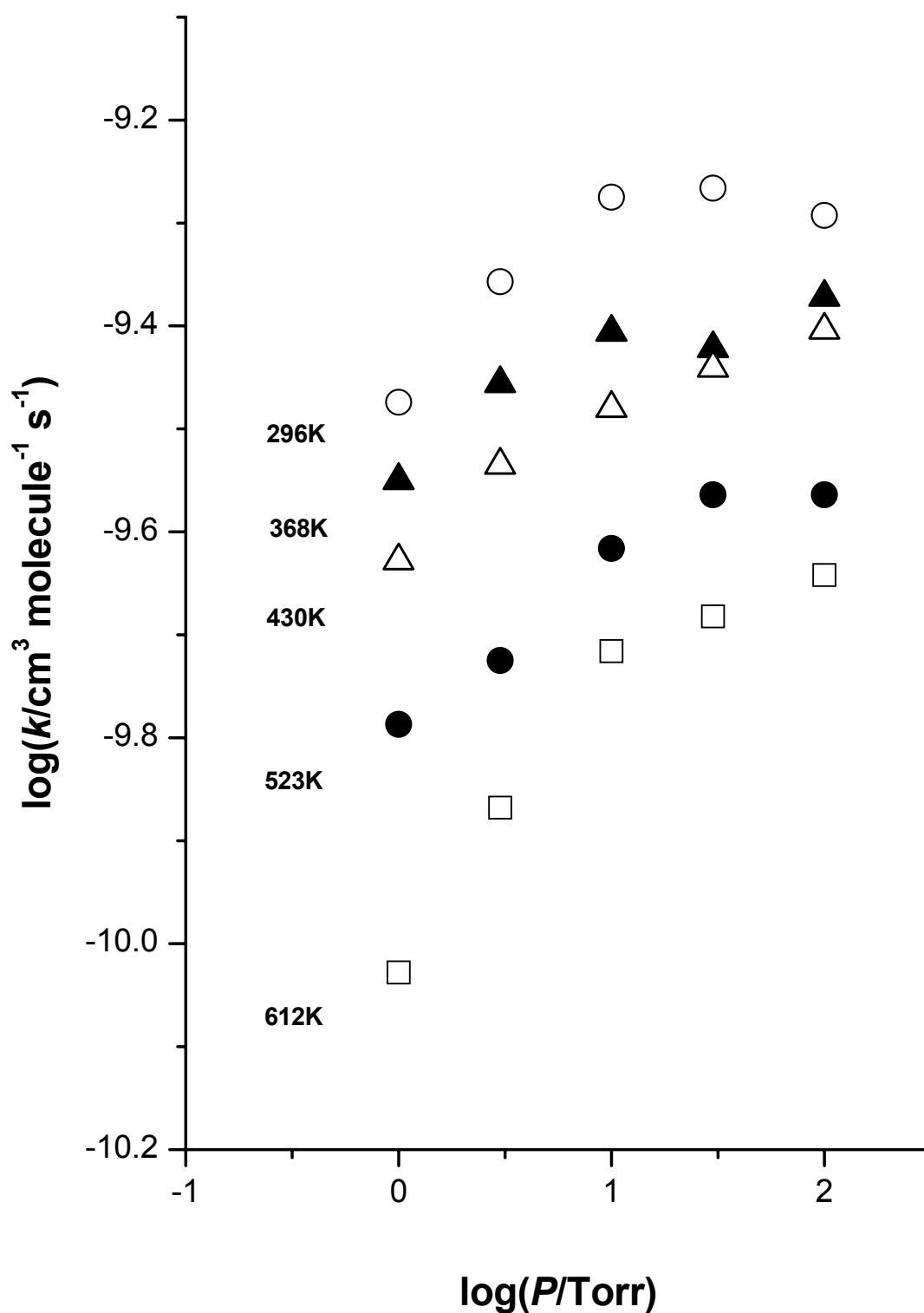


Fig. S3 Pressure dependence of second order rate constants for reaction (D), $\text{SiD}_2 + \text{MeC}\equiv\text{CMe}$, in the presence of SF_6 at five temperatures (indicated).